

DATA SHEET

BYV42E, BYV42EB series

Rectifier diodes
ultrafast, rugged

Product specification

September 2018



WeEn
WeEn Semiconductors

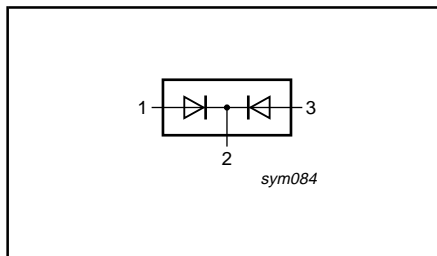
**Rectifier diodes
ultrafast, rugged**

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FEATURES

- Low forward volt drop
- Fast switching
- Soft recovery characteristic
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$V_R = 150 \text{ V} / 200 \text{ V}$
$V_F \leq 0.85 \text{ V}$
$I_{O(AV)} = 30 \text{ A}$
$I_{RRM} = 0.2 \text{ A}$
$t_r \leq 28 \text{ ns}$

GENERAL DESCRIPTION

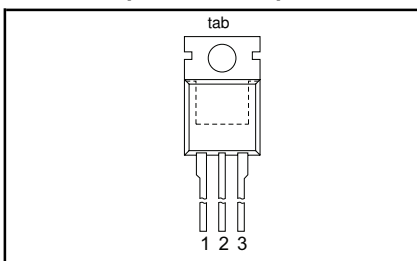
Dual, ultra-fast, epitaxial rectifier diodes intended for use as output rectifiers in high frequency switched mode power supplies.

The BYV42E series is supplied in the SOT78 conventional leaded package.
The BYV42EB series is supplied in the SOT404 surface mounting package.

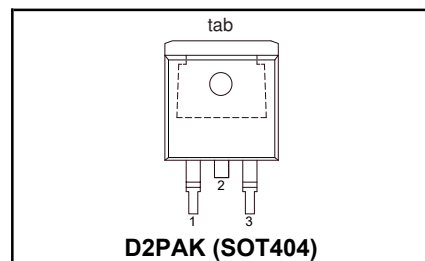
PINNING

PIN	DESCRIPTION
1	anode 1 (a)
2	cathode (k) ¹
3	anode 2 (a)
tab	cathode (k)

SOT78 (TO220AB)



SOT404



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V_{RRM} V_{RWM} V_R	Peak repetitive reverse voltage	BYV42E / BYV42EB $T_{mb} \leq 144^\circ\text{C}$	-	-150	-200	V
	Crest working reverse voltage			150	200	
	Continuous reverse voltage			150	200	
$I_{O(AV)}$	Average rectified output current (both diodes conducting)	square wave $\delta = 0.5; T_{mb} \leq 108^\circ\text{C}$	-	30		A
I_{FRM}	Repetitive peak forward current per diode	$t = 25 \mu\text{s}; \delta = 0.5;$ $T_{mb} \leq 108^\circ\text{C}$	-	30		A
I_{FSM}	Non-repetitive peak forward current per diode	$t = 10 \text{ ms}$	-	150		A
		$t = 8.3 \text{ ms}$ sinusoidal; with reapplied	-	160		A
I_{RRM}	Repetitive peak reverse current per diode	$V_{RWM(max)}$ $t_p = 2 \mu\text{s}; \delta = 0.001$	-	0.2		A
I_{RSM}	Non-repetitive peak reverse current per diode	$t_p = 100 \mu\text{s}$	-	0.2		A
T_{stg}	Storage temperature		-40	150		$^\circ\text{C}$
T_j	Operating junction temperature		-	150		$^\circ\text{C}$

1. It is not possible to make connection to pin 2 of the SOT404 package
2. SOT78 package, For output currents in excess of 20 A, the cathode connection should be made to the mounting tab.

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ESD LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_C	Electrostatic discharge capacitor voltage	Human body model; $C = 250 \text{ pF}$; $R = 1.5 \text{ k}\Omega$	-	8	kV

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	per diode	-	-	2.4	K/W
		both diodes	-	-	1.4	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	SOT78 package, in free air	-	60	-	K/W
		SOT404 and SOT428 packages, pcb mounted, minimum footprint, FR4 board	-	50	-	K/W

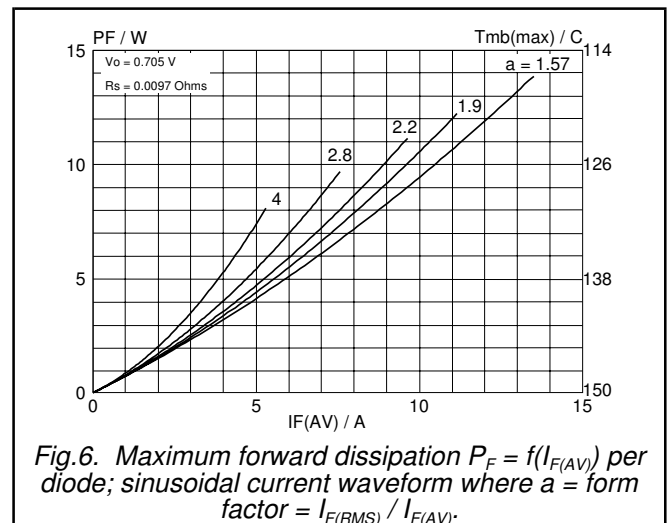
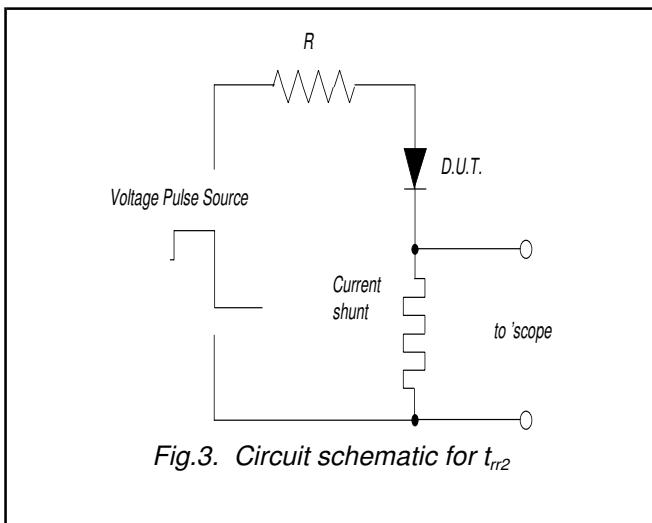
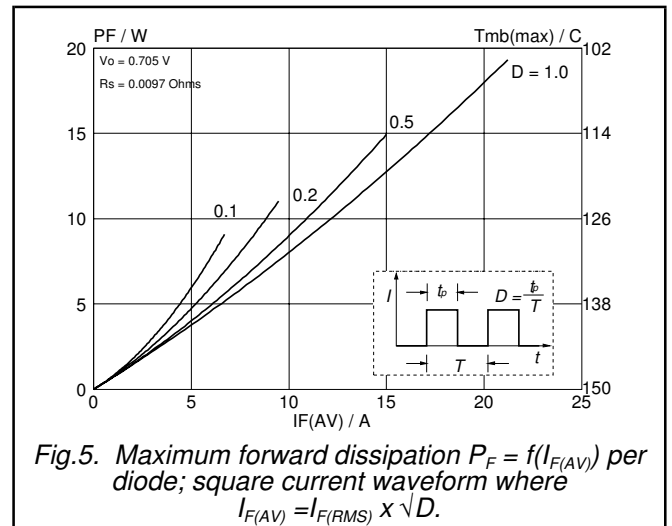
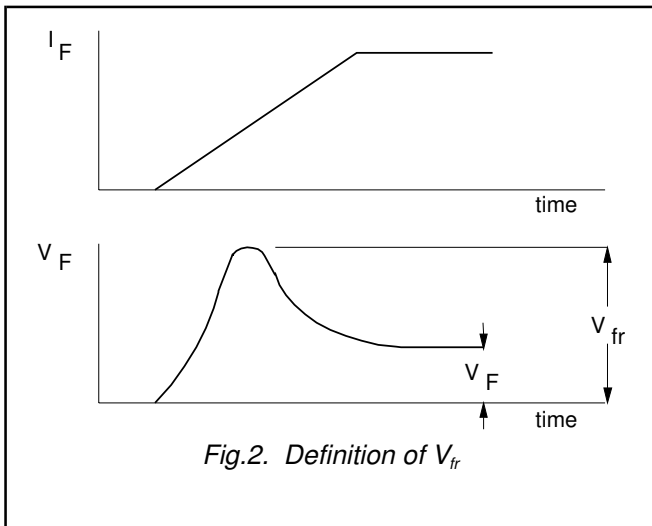
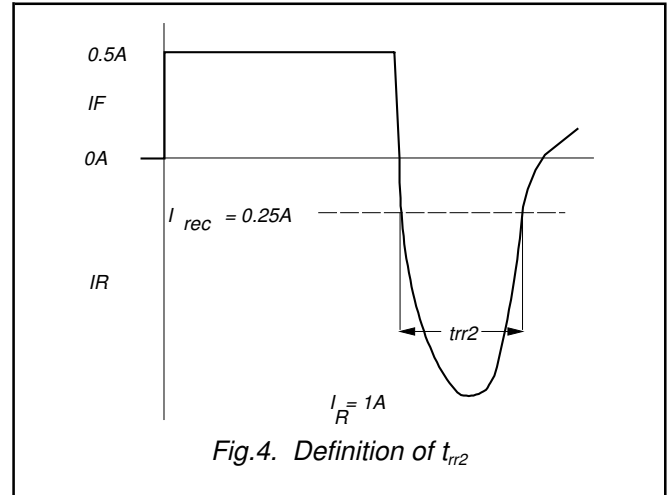
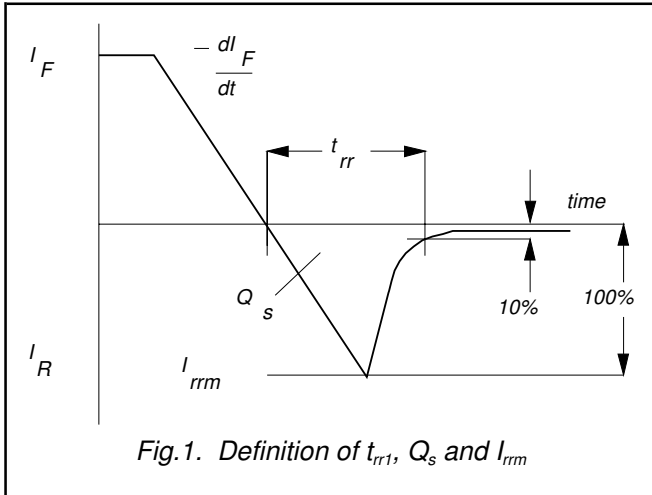
ELECTRICAL CHARACTERISTICS

characteristics are per diode at $T_j = 25 \text{ }^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	Forward voltage	$I_F = 15 \text{ A}$; $T_j = 150 \text{ }^\circ\text{C}$	-	0.78	0.85	V
		$I_F = 15 \text{ A}$	-	0.95	1.05	V
		$I_F = 30 \text{ A}$	-	1.00	1.20	V
I_R	Reverse current	$V_R = V_{RWM}$; $T_j = 100 \text{ }^\circ\text{C}$	-	0.5	1	mA
		$V_R = V_{RWM}$	-	10	100	μA
Q_s	Reverse recovery charge	$I_F = 2 \text{ A}$; $V_R \geq 30 \text{ V}$; $-di_F/dt = 20 \text{ A}/\mu\text{s}$	-	6	15	nC
t_{rr1}	Reverse recovery time	$I_F = 1 \text{ A}$; $V_R \geq 30 \text{ V}$; $-di_F/dt = 100 \text{ A}/\mu\text{s}$	-	20	28	ns
t_{rr2}	Reverse recovery time	$I_F = 0.5 \text{ A}$ to $I_R = 1 \text{ A}$; $I_{rec} = 0.25 \text{ A}$	-	13	22	ns
V_{fr}	Forward recovery voltage	$I_F = 1 \text{ A}$; $di_F/dt = 10 \text{ A}/\mu\text{s}$	-	1	-	V

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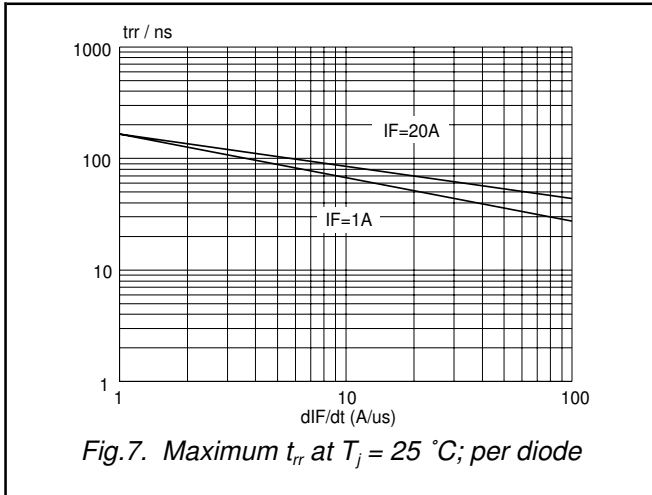


Fig.7. Maximum t_{rr} at $T_j = 25^\circ C$; per diode

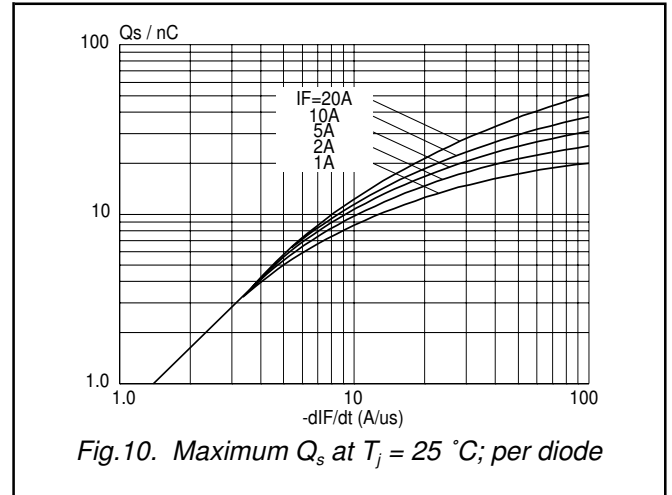


Fig.10. Maximum Q_s at $T_j = 25^\circ C$; per diode

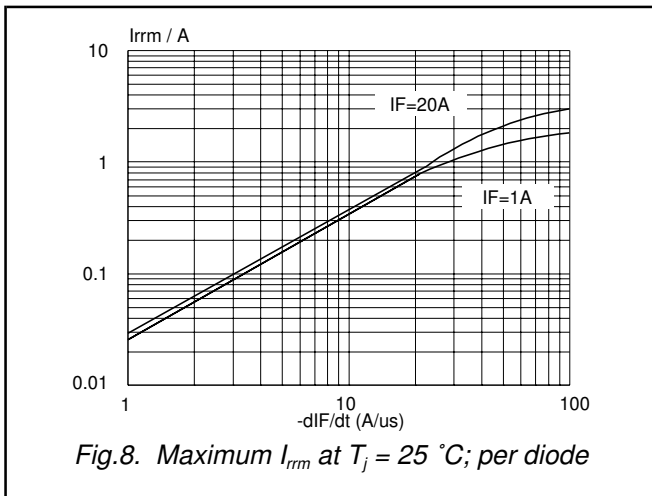


Fig.8. Maximum I_{rrm} at $T_j = 25^\circ C$; per diode

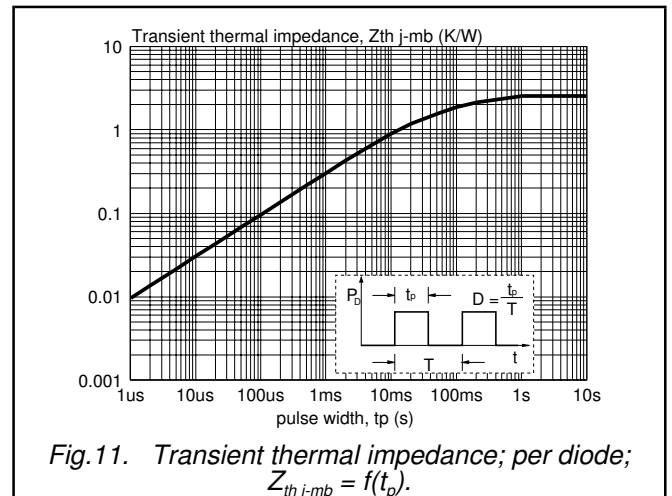


Fig.11. Transient thermal impedance; per diode;
 $Z_{th\ j-mb} = f(t_p)$.

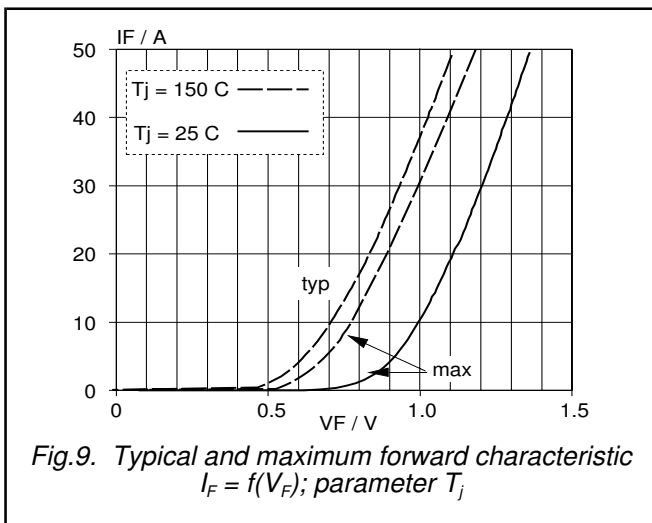


Fig.9. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_j

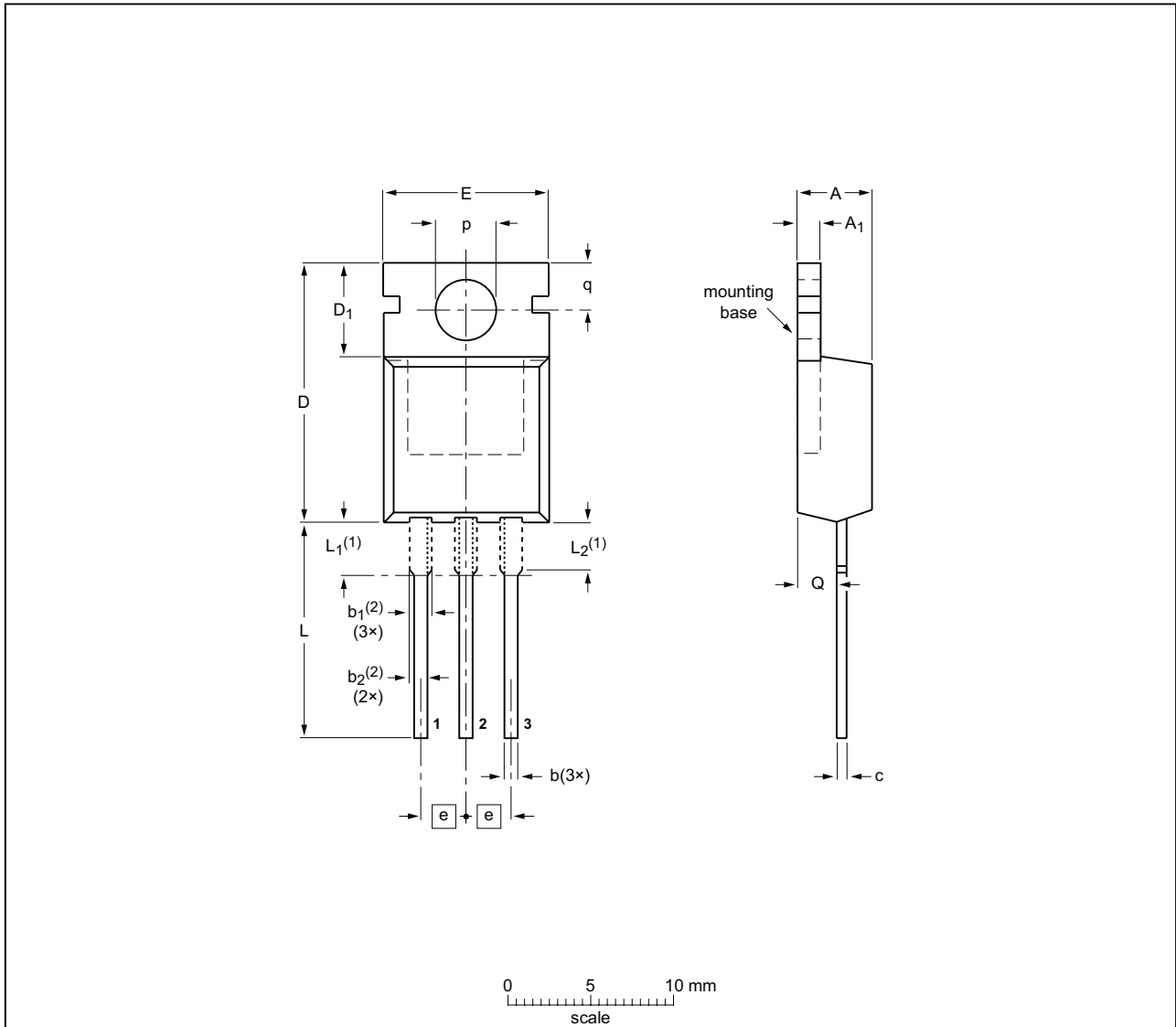
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MECHANICAL DATA

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (²)	b ₂ (²)	c	D	D ₁	E	e	L	L ₁ (¹)	L ₂ (¹) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

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MECHANICAL DATA

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

TO263

